RoHS Compliant

Magnachip

MDS1527

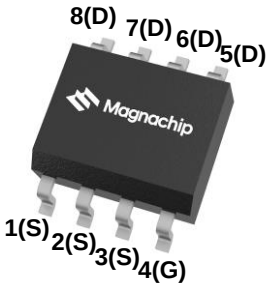
Single N-channel Trench MOSFET 30V, 13.1A, 15.9mΩ

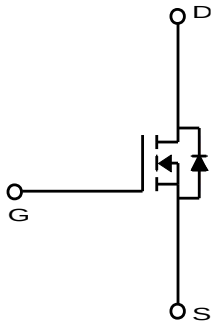
General Description

The MDS1527 uses advanced Magnachip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDS1527 is suitable for DC/DC converter and general purpose applications.

Features

- V_{DS} = 30V
- I_D = 13.1A @V_{GS} = 10V
- $R_{DS(ON)}$
  < 15.9mΩ @V_{GS} = 10V
  < 23.7mΩ @V_{GS} = 4.5V
- 100% UIL Tested
- 100% Rg Tested





Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (1)	T_C=25°C	I_D	13.1	A
	T_C=70°C		10.3	
	T_A=25°C		9.4(3)	
	T_A=70°C		7.5(3)	
Pulsed Drain Current		I_{DM}	40	A
Power Dissipation	T_C=25°C	P_D	4.8	W
	T_C=70°C		3.0	
	T_A=25°C		2.5(3)	
	T_A=70°C		1.6(3)	
Single Pulse Avalanche Energy (2)		E_{AS}	23.1	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	°C

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient (1)	$R_{\theta JA}$	50	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	23.2	

Ordering Information

Part Number	Temp. Range	Package	Packing	Quantity	Rohs Status
MDS1527URH	-55~150°C	SOIC-8	Tape & Reel	3000 units	Halogen Free

Electrical Characteristics (T_J = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D = 250μA, V_{GS} = 0V	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.3	1.9	2.7	V
Drain Cut-Off Current	I_{DSS}	V_{DS} = 30V, V_{GS} = 0V	-	-	1	μA
		T_J=55°C	-	-	5	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V	-	-	±0.1	μA
Drain-Source ON Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 7A	-	13.8	15.9	mΩ
		T_J=125°C	-	20.0	23.1	mΩ
		V_{GS} = 4.5V, I_D = 6A	-	19.7	23.7	mΩ
Forward Transconductance	g_{fs}	V_{DS} = 5V, I_D = 7A	-	20.3	-	S
Dynamic Characteristics						
Total Gate Charge	$Q_{g(10V)}$	V_{DS} = 15.0V, I_D = 7A, V_{GS} = 10V	5.5	7.8	10.2	nC
Total Gate Charge	$Q_{g(4.5V)}$		2.6	3.7	4.9	nC
Gate-Source Charge	Q_{gs}		-	1.7	-	nC
Gate-Drain Charge	Q_{gd}		-	1.2	-	nC
Input Capacitance	C_{iss}	V_{DS} = 15.0V, V_{GS} = 0V, f = 1.0MHz	337	481	625	pF
Reverse Transfer Capacitance	C_{rss}		33	47	61	pF
Output Capacitance	C_{oss}		69	99	128	pF
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = 10V, V_{DS} = 15.0V, I_D = 7A, R_G = 3.0Ω	-	5.2	-	ns
Rise Time	t_r		-	10.7	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	14.1	-	ns
Fall Time	t_f		-	4.8	-	ns
Gate Resistance	R_g	f=1 MHz	1.0	2.9	4.0	Ω
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V_{SD}	I_S = 7A, V_{GS} = 0V	-	0.84	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 7A, dI/dt = 100A/μs	-	16.3	24.4	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	8.2	12.3	nC

Note :

1. Surface mounted FR-4 board by JEDEC (jesd51-7)
2. E_{AS} is tested at starting Tj = 25℃, L = 0.1mH, I_{AS} = 11.6A, V_{DD} = 27V, V_{GS} = 10V.
3. T < 10sec.

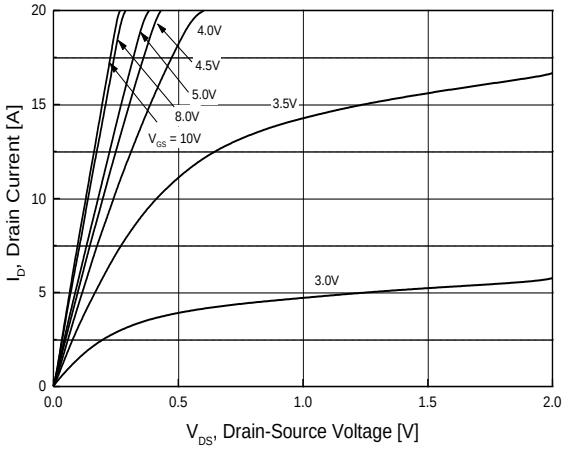


Fig.1 On-Region Characteristics

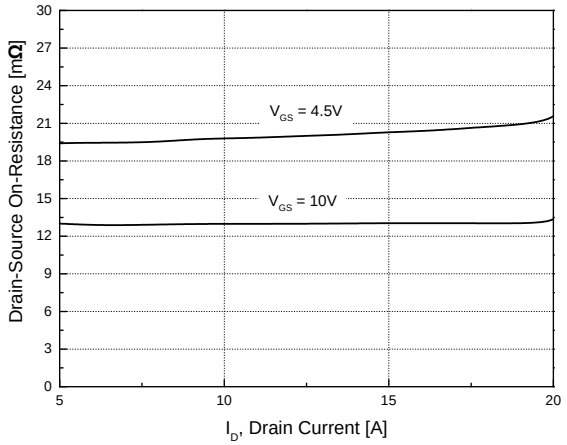


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

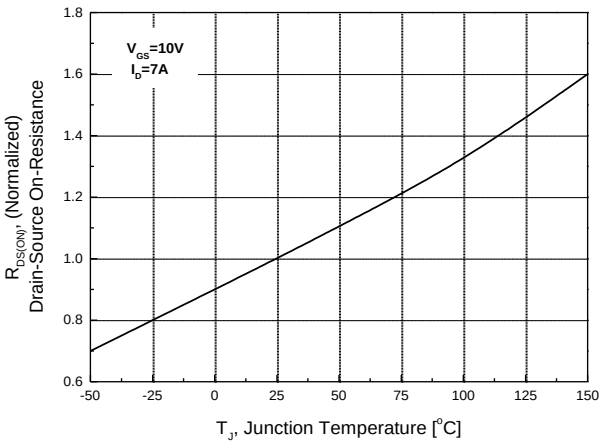


Fig.3 On-Resistance Variation with Temperature

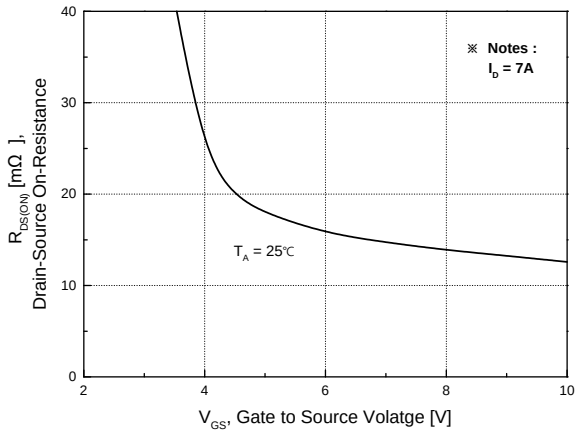


Fig.4 On-Resistance Variation with Gate to Source Voltage

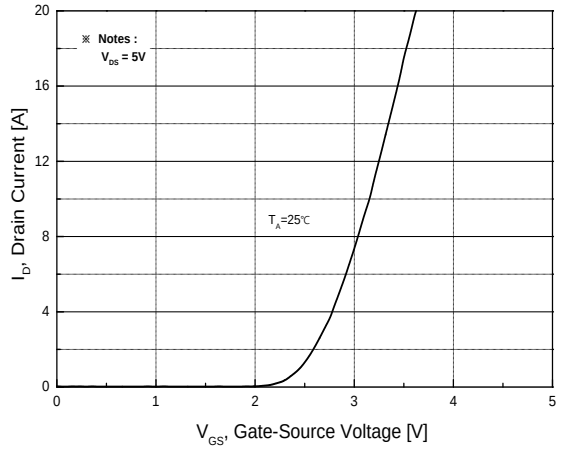


Fig.5 Transfer Characteristics

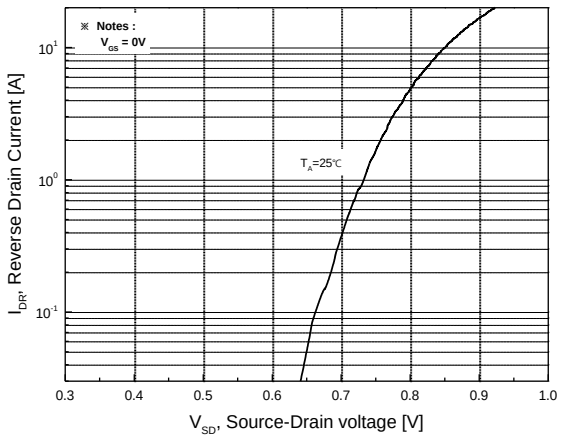


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

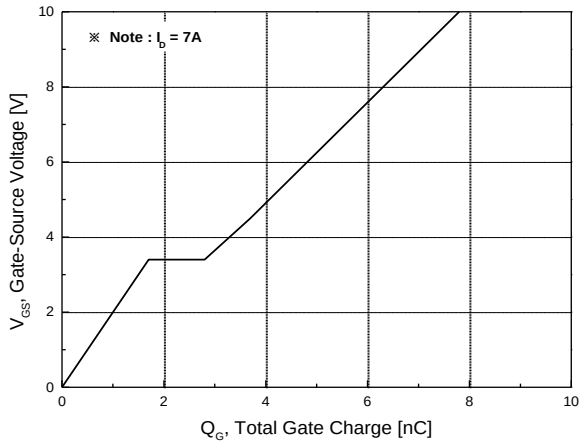


Fig.7 Gate Charge Characteristics

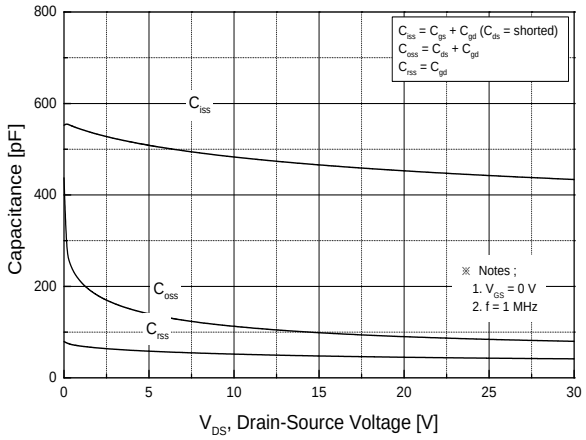


Fig.8 Capacitance Characteristics

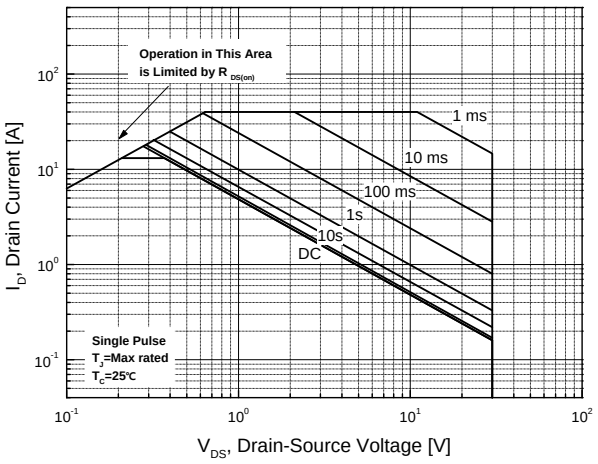


Fig.9 Maximum Safe Operating Area

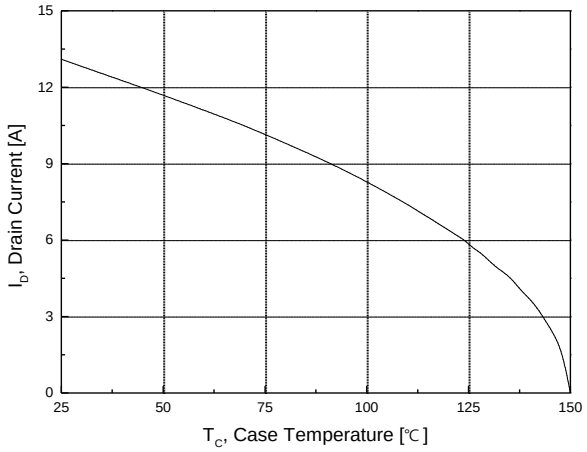


Fig.10 Maximum Drain Current vs. Case Temperature

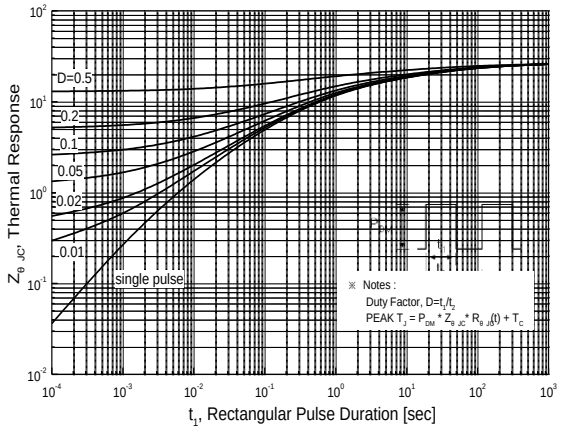
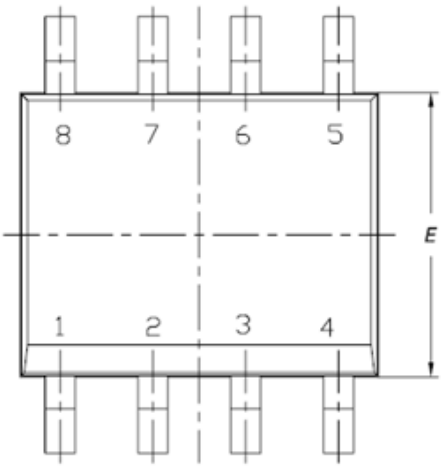


Fig.11 Transient Thermal Response Curve

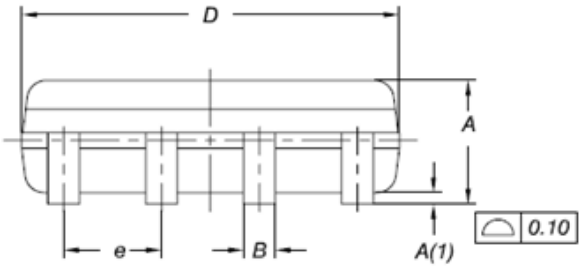
Physical Dimensions

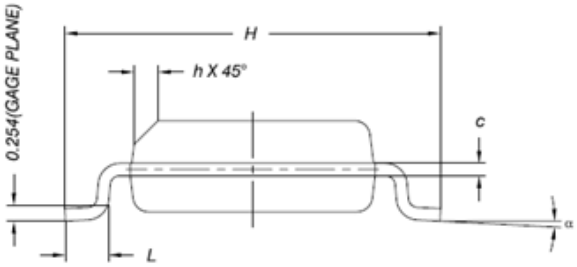
SOIC-8L

Dimensions are in millimeters unless otherwise specified



Symbol	Min	Nom	Max
A	-	-	1.75
A(1)	0.10	-	0.25
B	0.31	-	0.51
C	0.10	-	0.25
D	4.9 BSC		
E	3.9 BSC		
e	1.27 BSC		
H	6.0 BSC		
L	0.40	-	1.27
a	0	-	8
h	0.250	-	0.500
L2(Gage plane)	0.25 BSC		





Note : Package body size, length and width do not include mold flash, protrusions and gate burrs.

DISCLAIMER:

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